

Device Modeling Report

COMPONENTS:
DIODE/GENERAL PURPOSE RECTIFIER/ PROFESSIONAL
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REMARK: TC=25C

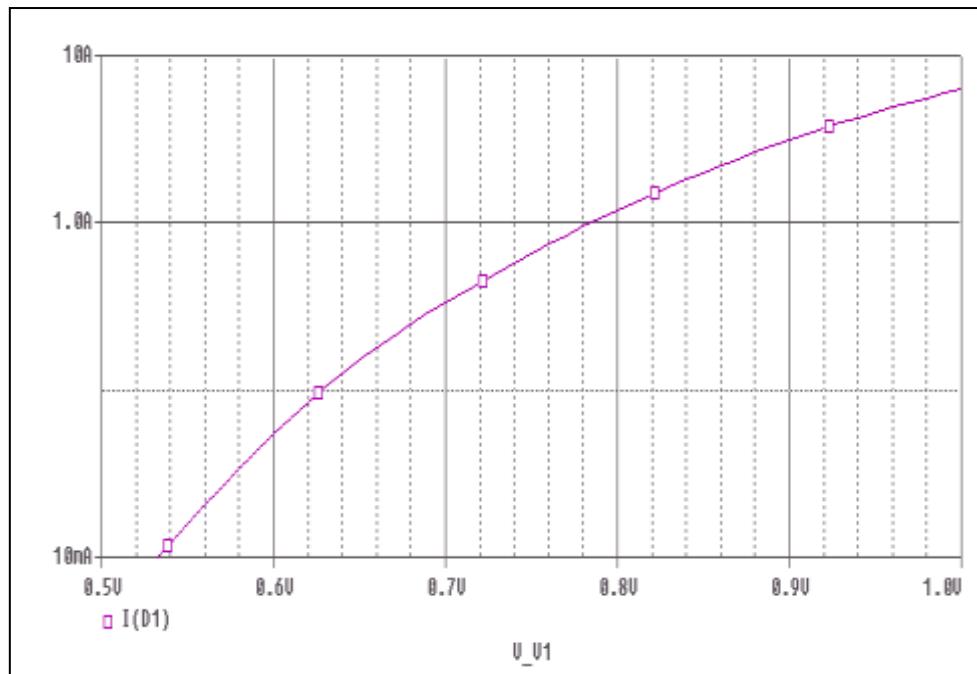


Bee Technologies Inc.

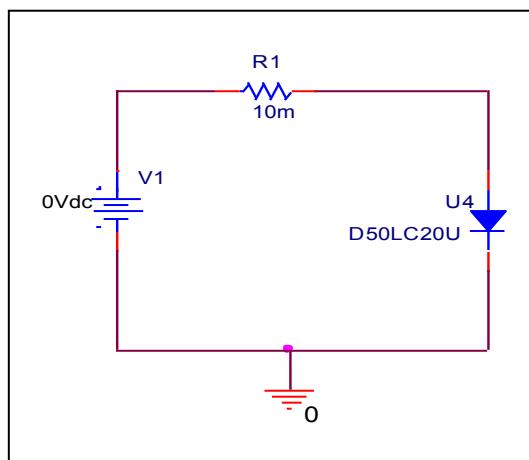
PSpice model parameter	Model description
IS	Saturation Current
N	Emission Coefficient
RS	Series Resistance
IKF	High-injection Knee Current
CJO	Zero-bias Junction Capacitance
M	Junction Grading Coefficient
VJ	Junction Potential
ISR	Recombination Current Saturation Value
BV	Reverse Breakdown Voltage(a positive value)
IBV	Reverse Breakdown Current(a positive value)
TT	Transit Time
EG	Energy-band Gap

Forward Current Characteristic

Circuit Simulation Result

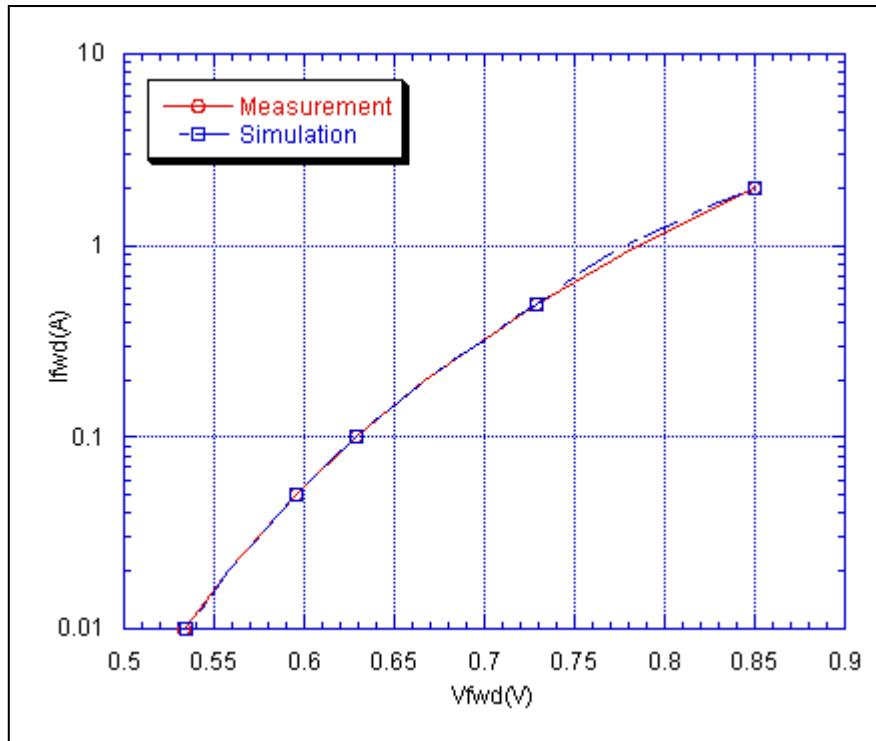


Evaluation circuit



Comparison graph

Circuit Simulation Result

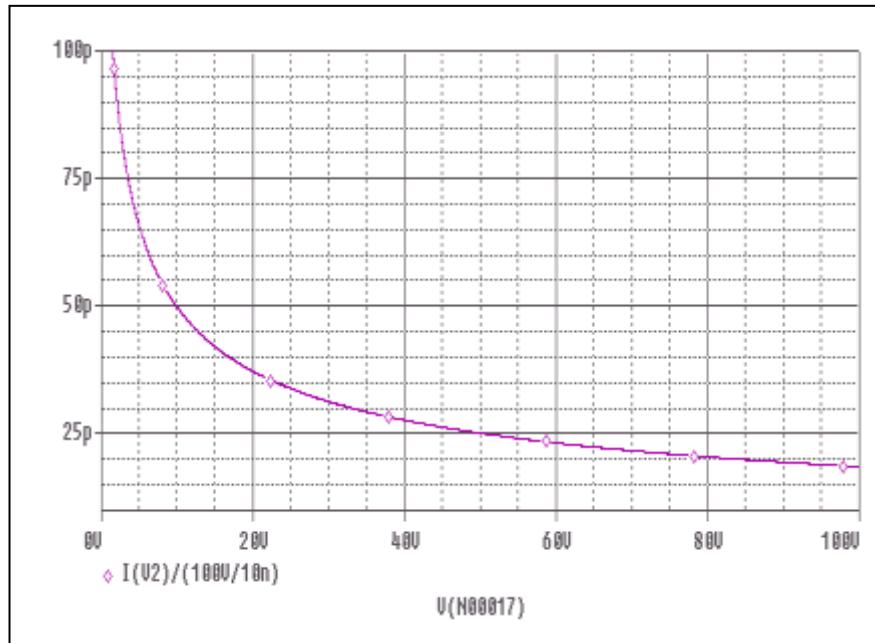


Simulation Result

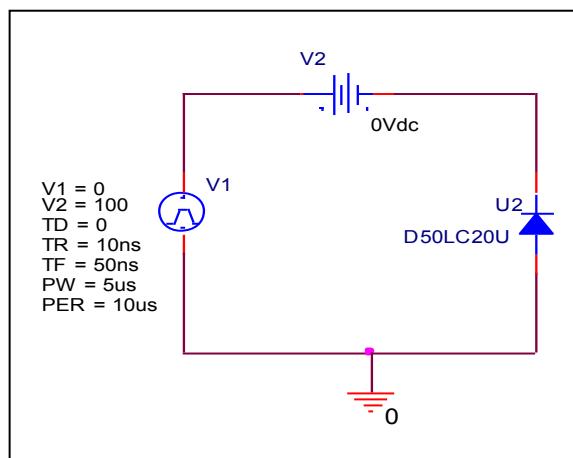
I_{fwd} (A)	V_{fwd} (V) Measurement	V_{fwd} (V) Simulation	%Error
0.01	0.533	0.534	-0.19
0.02	0.558	0.558	0.00
0.05	0.596	0.596	0.00
0.1	0.629	0.629	0.00
0.2	0.667	0.667	0.00
0.5	0.729	0.729	0.00
1	0.784	0.777	0.89
2	0.850	0.850	0.00

Junction Capacitance Characteristic

Circuit Simulation Result

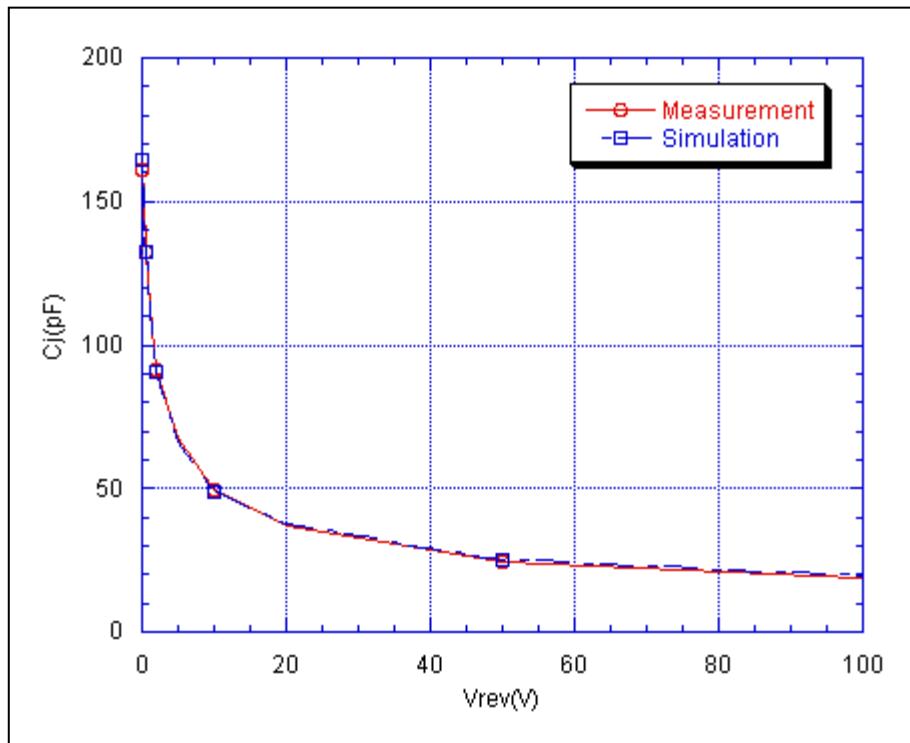


Evaluation circuit



Comparison graph

Circuit Simulation Result

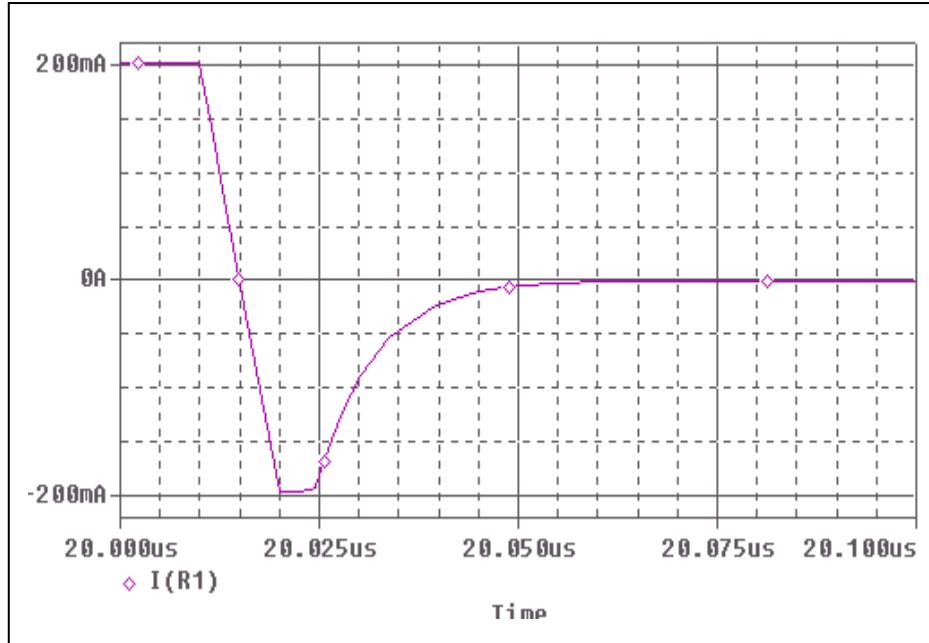


Simulation Result

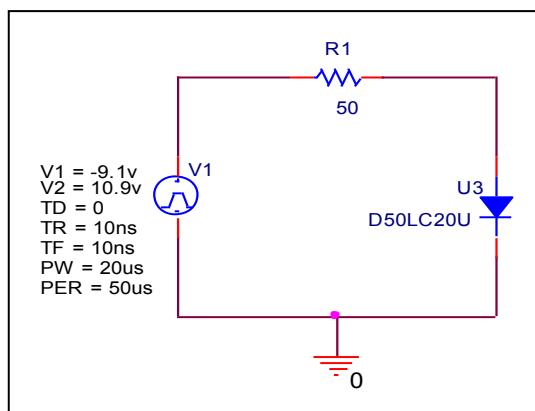
V_{rev} (V)	C_j (pF) Measurement	C_j (pF) Simulation	%Error
0	171.100	171.100	0.00
0.1	161.080	164.148	-1.90
0.2	151.940	151.313	0.41
0.5	132.450	132.190	0.20
1	113.360	113.945	-0.52
2	91.239	90.893	0.38
5	67.456	66.025	2.12
10	49.853	49.157	1.40
20	37.106	37.358	-0.68
50	24.760	25.165	-1.64
100	18.178	18.569	-2.15

Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation circuit

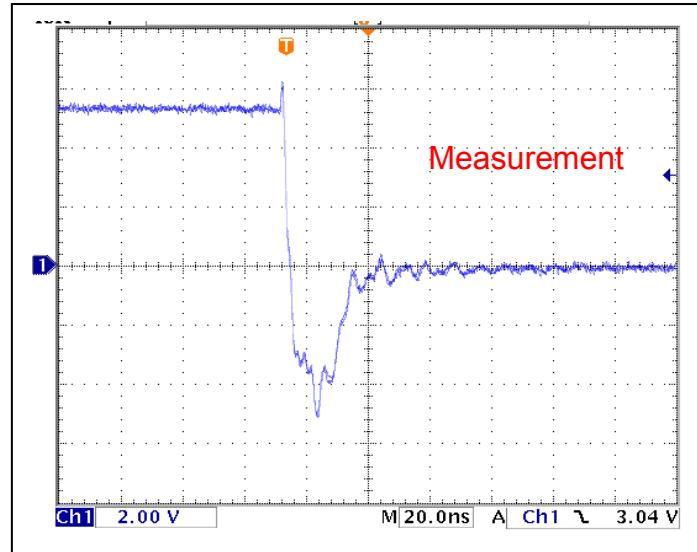


Compare Measurement vs. Simulation

	Measurement		Simulation		Error (%)
trj	8.80	ns	8.81	ns	0.159
trb	16.40	ns	16.49	ns	0.597

Reverse Recovery Characteristic

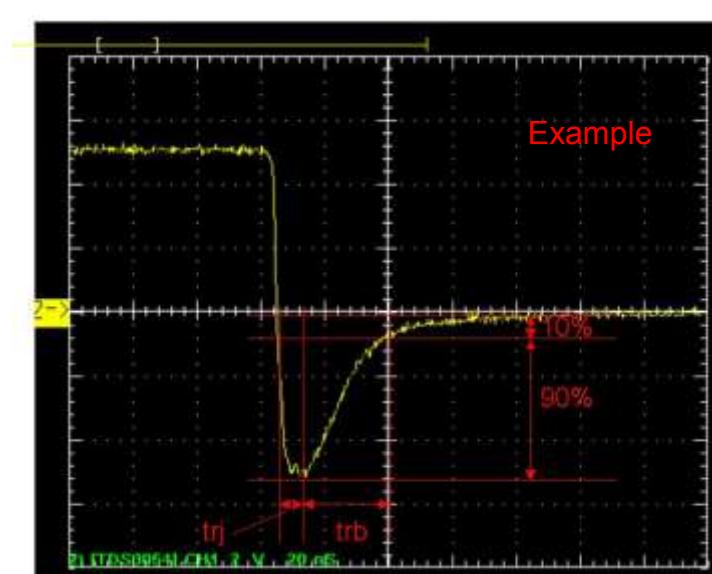
Reference



$trj=8.8(\text{ns})$

$trb=16.4(\text{ns})$

Conditions: Ifwd=Irev=0.2(A), RI=50



Relation between trj and trb